



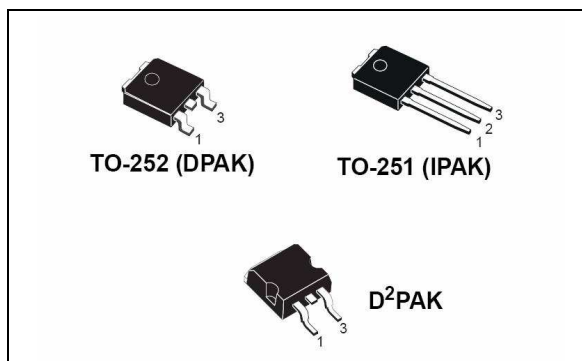
VNB14NV04, VND14NV04 VND14NV04-1

"OMNIFET II"
fully autoprotected Power MOSFET

Features

TYPE	$R_{DS(on)}$	I_{lim}	V_{clamp}
VNB14NV04 VND14NV04 VND14NV04-1	35 m Ω	12 A	40 V

- Linear current limitation
- Thermal shutdown
- Short circuit protection
- Integrated clamp
- Low current drawn from input pin
- Diagnostic feedback through input pin
- ESD protection
- Direct access to the gate of the Power MOSFET (analog driving)
- Compatible with standard Power MOSFET



Description

The VNB14NV04, VND14NV04, VND14NV04-1 are monolithic devices made using STMicroelectronics VIPower M0 Technology, intended for replacement of standard power MOSFETS in DC to 50 KHz applications. Built-in thermal shutdown, linear current limitation and overvoltage clamp protect the chip in harsh environments.

Fault feedback can be detected by monitoring the voltage at the input pin.

Table 1. Device summary

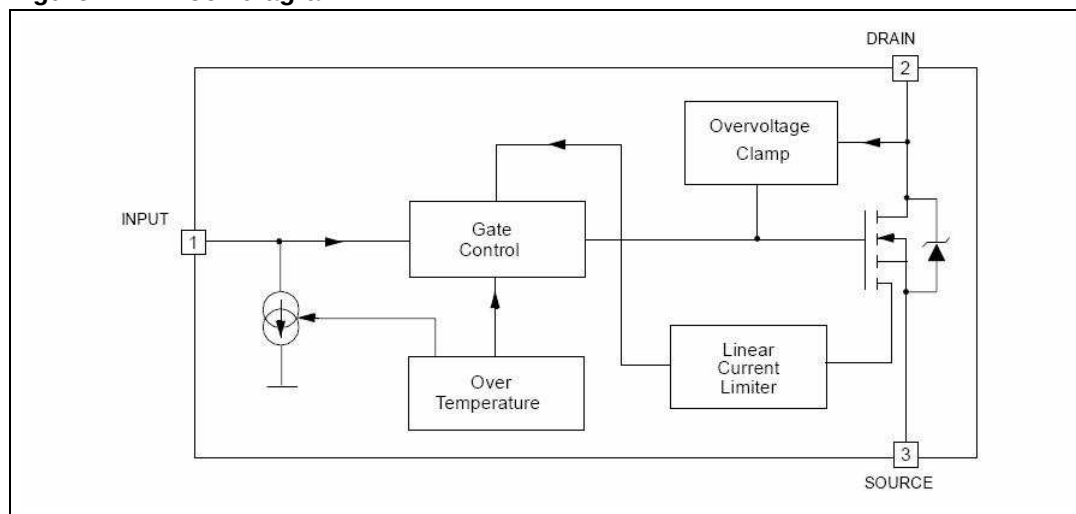
Package	Tube	Tube (Lead free)	Tape and reel	Tape and reel (Lead free)
D2PAK	VNB14NV04	VNB14NV04-E	VNB14NV0413TR	VNB14NV04TR-E
TO-252 (DPAK)	VND14NV04	VND14NV04-E	VND14NV0413TR	VND14NV04TR-E
TO-251 (IPAK)	VND14NV04-1	VND14NV04-1-E	-	-

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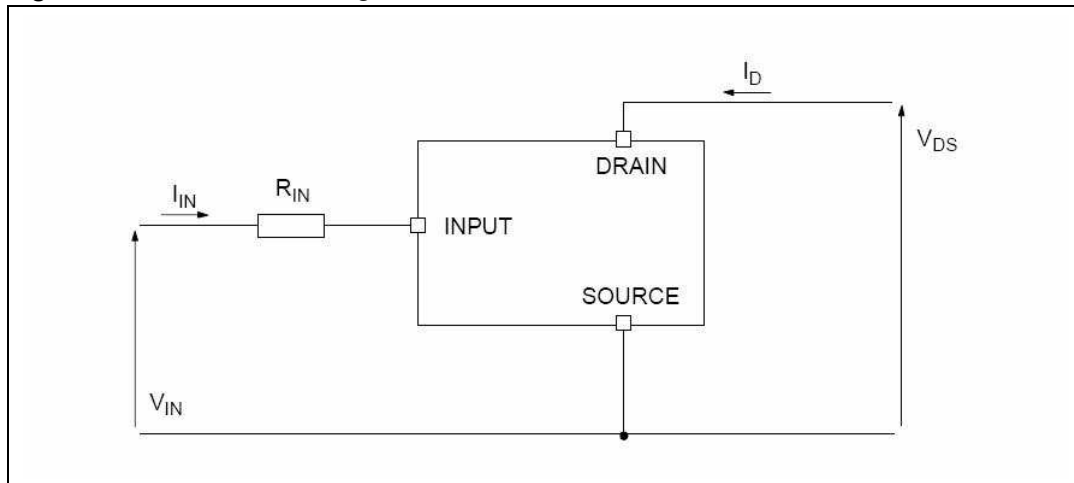
1 Block diagram

Figure 1. Block diagram



2 Electrical specification

Figure 2. Current and voltage conventions



2.1 Absolute maximum rating

Table 2. Absolute maximum rating

Symbol	Parameter	Value			Unit
		DPAK	IPAK	D ² PAK	
V_{DS}	Drain-source voltage ($V_{IN}=0$ V)	Internally Clamped			V
V_{IN}	Input voltage	Internally Clamped			V
I_{IN}	Input current	+/-20			mA
$R_{IN\ MIN}$	Minimum input series impedance	10			Ω
I_D	Drain current	Internally Limited			A
I_R	Reverse DC output current	-15			A
V_{ESD1}	Electrostatic discharge ($R=1.5\ K\Omega$, $C=100\ pF$)	4000			V
V_{ESD2}	Electrostatic discharge on output pin only ($R=330\ \Omega$, $C=150\ pF$)	16500			V
P_{tot}	Total dissipation at $T_c=25\ ^\circ C$	74	74	74	W
E_{MAX}	Maximum switching energy ($L=0.4\ mH$; $R_L=0\ \Omega$; $V_{bat}=13.5\ V$; $T_{jstart}=150\ ^\circ C$; $I_L=18\ A$)	93		93	mJ
T_j	Operating junction temperature	Internally limited			$^\circ C$
T_c	Case operating temperature	Internally limited			$^\circ C$
T_{stg}	Storage temperature	-55 to 150			$^\circ C$

2.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	IPAK	D ² PAK	
R _{thj-case}	Thermal resistance junction-case max	1.7	1.7	1.7	°C/W
R _{thj-lead}	Thermal resistance junction-lead max				°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	65 ⁽¹⁾	102	52 ⁽¹⁾	°C/W

1. When mounted on a standard single-sided FR4 board with 0.5cm² of Cu (at least 35 µm thick) connected to all DRAIN pins. Horizontal mounting and no artificial air flow.

2.3 Electrical characteristics

-40 < T_j < 150 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off						
V _{CLAMP}	Drain-source clamp voltage	V _{IN} =0 V; I _D =7 A	40	45	55	V
V _{CLTH}	Drain-source clamp threshold voltage	V _{IN} =0 V; I _D =2 mA	36			V
V _{INTH}	Input threshold voltage	V _{DS} =V _{IN} ; I _D =1 mA	0.5		2.5	V
I _{ISS}	Supply current from input pin	V _{DS} =0 V; V _{IN} =5 V		100	150	µA
V _{INCL}	Input-source clamp voltage	I _{IN} =1 mA I _{IN} =-1 mA	6 -1.0	6.8	8 -0.3	V
I _{DSS}	Zero input voltage drain current (V _{IN} =0 V)	V _{DS} =13 V; V _{IN} =0 V; T _j =25 °C V _{DS} =25 V; V _{IN} =0 V			30 75	µA
On						
R _{DS(on)}	Static drain-source on resistance	V _{in} = 5 V I _D = 7 A T _j = 25 °C V _{in} = 5 V I _D = 7 A			35 70	mΩ
Dynamic (T_j=25°C, unless otherwise specified)						
g _{fs} ⁽¹⁾	Forward transconductance	V _{DD} = 13 V I _D = 7 A		18		S
C _{oss}	Output capacitance	V _{DS} = 13 V f = 1 MHz V _{IN} = 0 V		400		pF
Switching						
t _{d(on)}	Turn-on delay time	V _{DD} = 15 V I _D = 7 A V _{gen} = 5 V R _{gen} = R _{IN MIN} = 10 Ω (see Figure 3)		80	250	ns
t _r	Rise time			350	1000	ns
t _{d(off)}	Turn-off delay time			450	1350	ns
t _f	Fall time			150	500	ns

Table 4. Electrical characteristics (continued)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 15 V I _d = 7 A V _{gen} = 5 V R _{gen} = 2.2 KΩ (see Figure 3)		1.5	4.5	μs
t _r	Rise time			9.7	30.0	μs
t _{d(off)}	Turn-off delay time				25.0	μs
t _f	Fall time			10.2	30.0	μs
(di/dt) _{on}	Turn-on current slope	V _{DD} = 15 V I _D = 7 A V _{gen} = 5 V R _{gen} = R _{IN MIN} =10 Ω		16		A/μs
Q _i	Total input charge	V _{DD} = 12 V I _D = 7 A V _{in} = 5 V; I _{gen} = 2.13 mA (see Figure 7)		36.8		nC
Source drain diode						
V _{SD} ⁽¹⁾	Forward on voltage	I _{SD} = 7 A V _{in} = 0 V		0.8		V
t _{rr}	Reverse recovery time	I _{SD} = 7 A; di/dt = 40 A/μs V _{DD} = 30 V L = 200 μH (see test circuit, Figure 4)		300		ns
Q _{rr}	Reverse recovery charge			0.8		μC
I _{RRM}	Reverse recovery current			5		A
Protection						
I _{lim}	Drain current limit	V _{IN} = 5 V; V _{DS} = 13 V	12	18	24	A
t _{dlim}	Step response current limit	V _{IN} = 5 V; V _{DS} = 13 V		45		μs
T _{jsh}	Over temperature shutdown		150	175	200	°C
T _{jrs}	Over temperature reset		135			°C
I _{gf}	Fault sink current	V _{IN} = 5 V; V _{DS} = 13 V; T _j = T _{jsh}	10	15	20	mA
E _{as}	Single pulse avalanche energy	starting T _j = 25 °C; V _{DD} = 24 V V _{IN} = 5 V; R _{gen} = R _{IN MIN} = 10 Ω; L = 24 mH (see Figure 5 and Figure 6)	400			mJ

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

3 Protection features

During normal operation, the input pin is electrically connected to the gate of the internal power MOSFET through a low impedance path.

The device then behaves like a standard power MOSFET and can be used as a switch from DC up to 50 KHz. The only difference from the user's standpoint is that a small DC current I_{SS} (typ. 100 μ A) flows into the input pin in order to supply the internal circuitry.

The device integrates:

- Overvoltage clamp protection: internally set at 45 V, along with the rugged avalanche characteristics of the Power MOSFET stage give this device unrivalled ruggedness and energy handling capability. This feature is mainly important when driving inductive loads.
- Linear current limiter circuit: limits the drain current I_D to I_{lim} whatever the input pin voltages. When the current limiter is active, the device operates in the linear region, so power dissipation may exceed the capability of the heatsink. Both case and junction temperatures increase, and if this phase lasts long enough, junction temperature may reach the over temperature threshold T_{jsh} .
- Over temperature and short circuit protection: these are based on sensing the chip temperature and are not dependent on the input voltage. The location of the sensing element on the chip in the power stage area ensures fast, accurate detection of the junction temperature. Over temperature cutout occurs in the range 150 to 190 $^{\circ}$ C, a typical value being 170 $^{\circ}$ C. The device is automatically restarted when the chip temperature falls of about 15 $^{\circ}$ C below shutdown temperature.
- Status feedback: in the case of an over temperature fault condition ($T_j > T_{jsh}$), the device tries to sink a diagnostic current I_{gf} through the input pin in order to indicate fault condition. If driven from a low impedance source, this current may be used in order to warn the control circuit of a device shutdown. If the drive impedance is high enough so that the input pin driver is not able to supply the current I_{gf} , the input pin will fall to 0 V. This will not however affect the device operation: no requirement is put on the current capability of the input pin driver except to be able to supply the normal operation drive current I_{SS} .

Additional features of this device are ESD protection according to the Human Body model and the ability to be driven from a TTL Logic circuit.

Figure 5. Unclamped inductive load test circuits

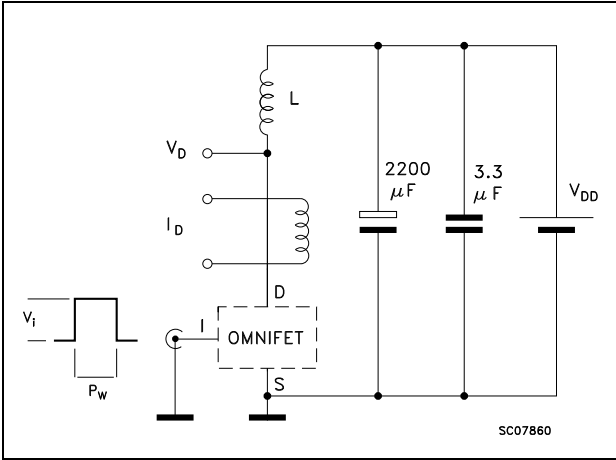


Figure 6. Unclamped inductive waveforms

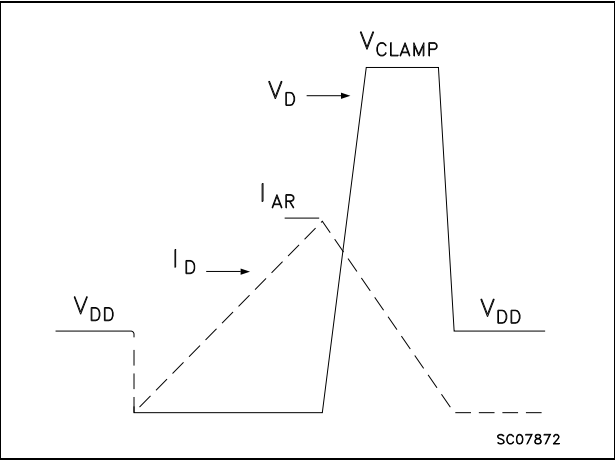


Figure 7. Input charge test circuit

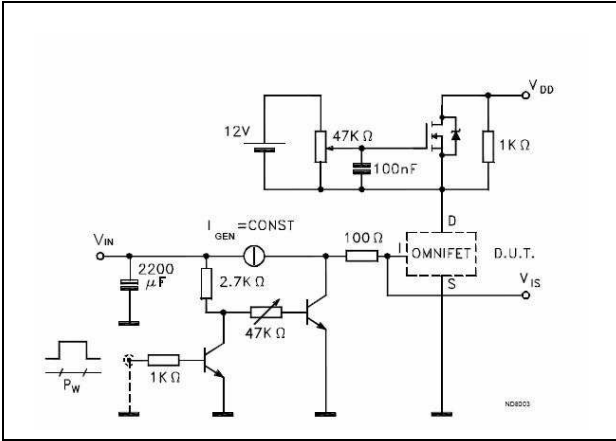


Figure 8. Source-drain diode forward characteristics

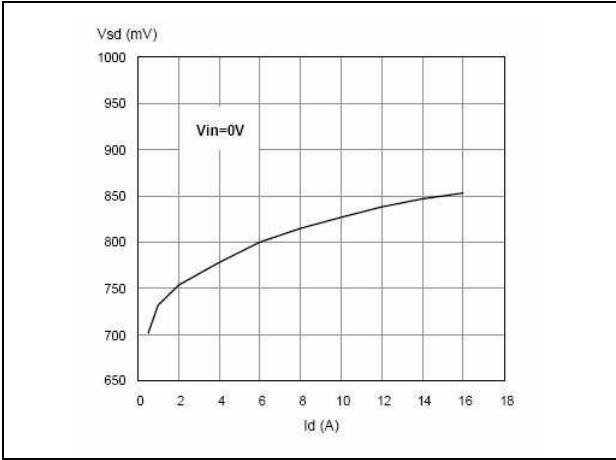


Figure 9. Static drain source on resistance

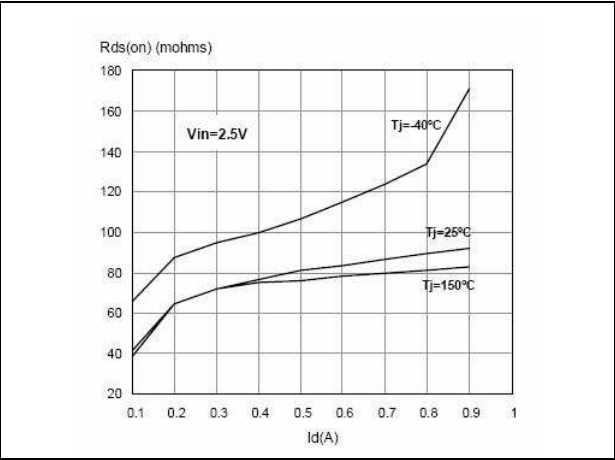


Figure 10. Derating curve

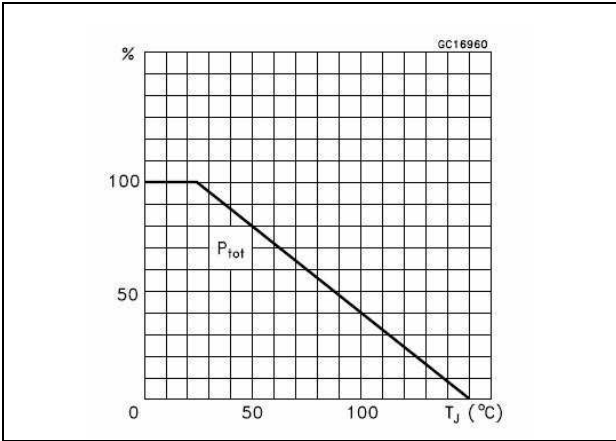


Figure 11. Static drain-source on resistance vs. input voltage (part 1/2)

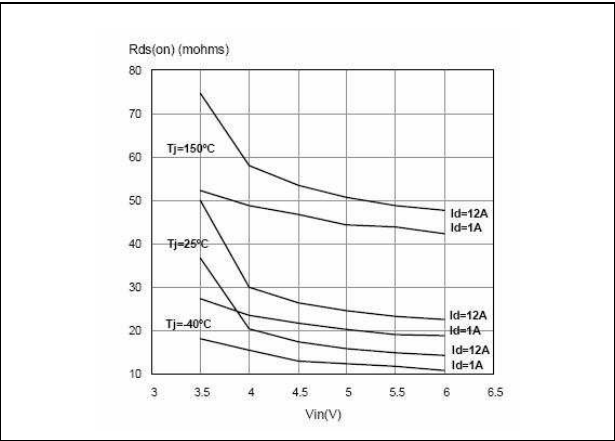


Figure 12. Static drain-source on resistance vs. input voltage (part 2/2)

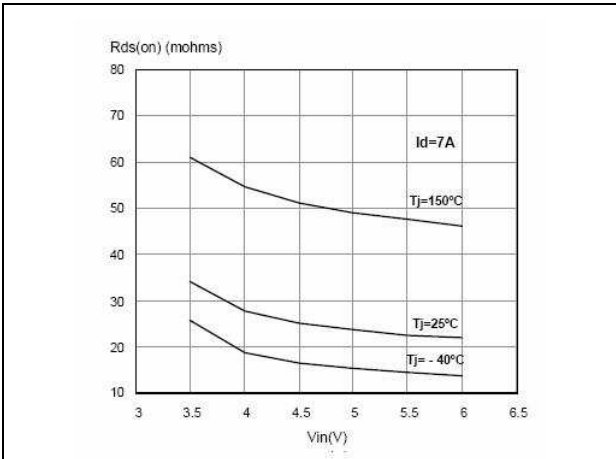


Figure 13. Transconductance

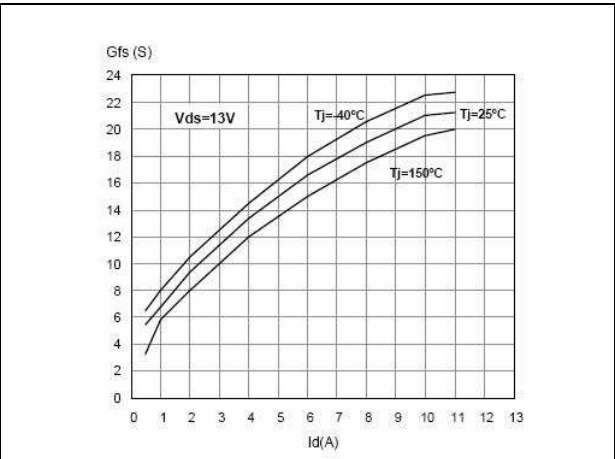


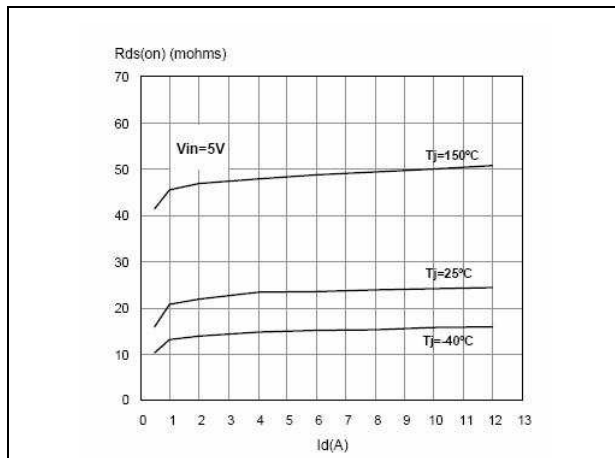
Figure 14. Static drain-source on resistance vs. I_D 

Figure 15. Transfer characteristics

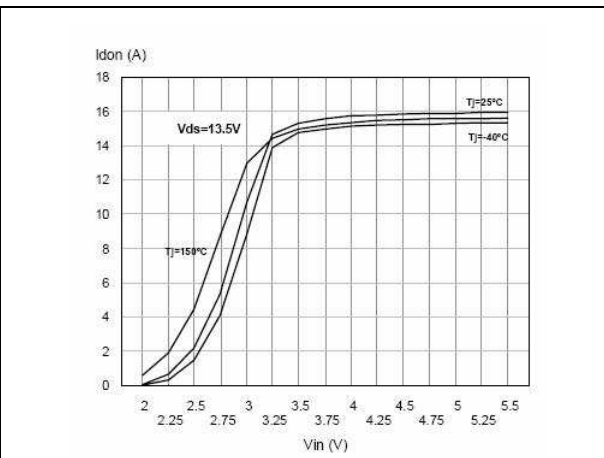


Figure 16. Turn-on current slope (part 1/2)

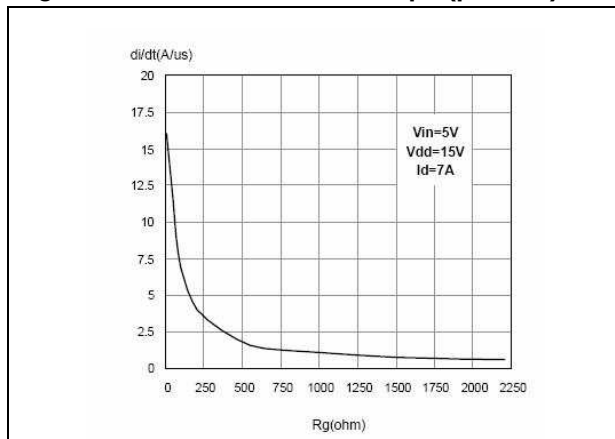


Figure 17. Turn-on current slope (part 2/2)

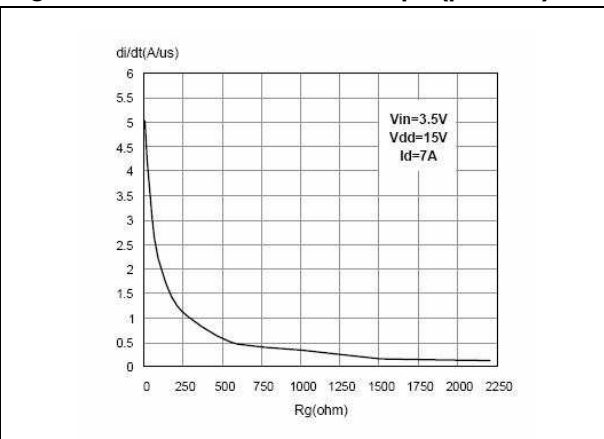


Figure 18. Input voltage vs. input charge

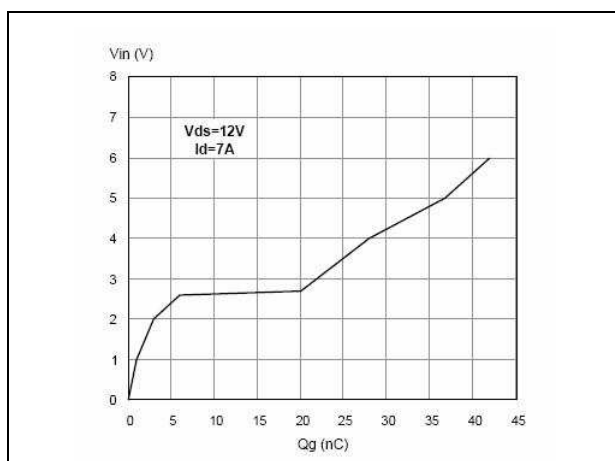


Figure 19. Turn-off drain source voltage slope (part 1/2)

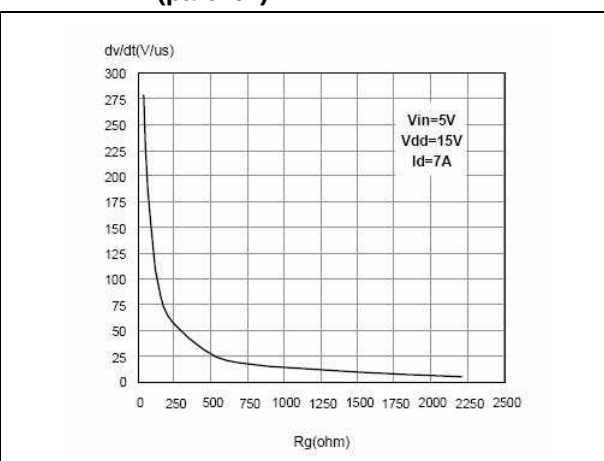


Figure 20. Turn-off drain source voltage slope Figure 21. Capacitance variations
(part 2/2)

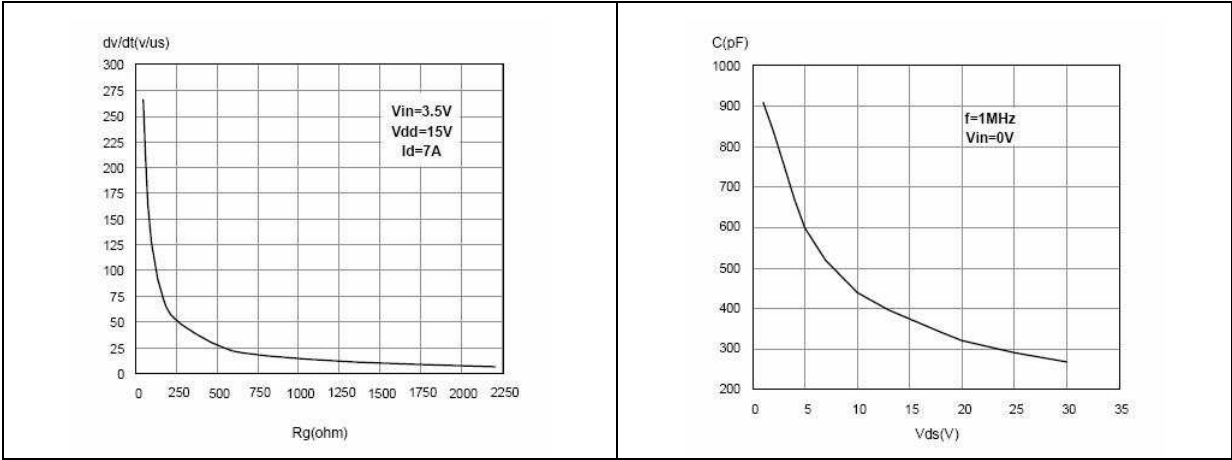


Figure 22. Switching time resistive load (part 1/2) Figure 23. Switching time resistive load (part 2/2)

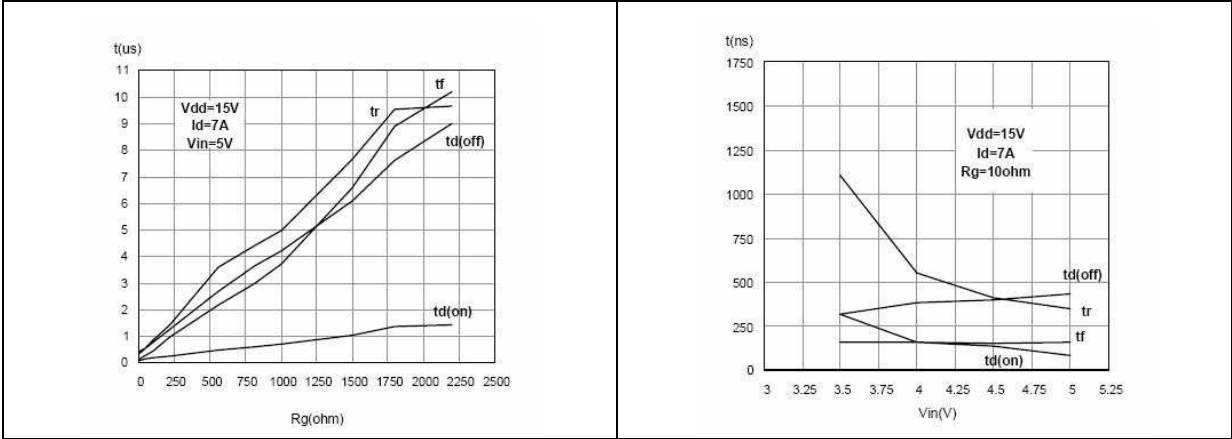


Figure 24. Output characteristics Figure 25. Normalized on resistance vs. temperature

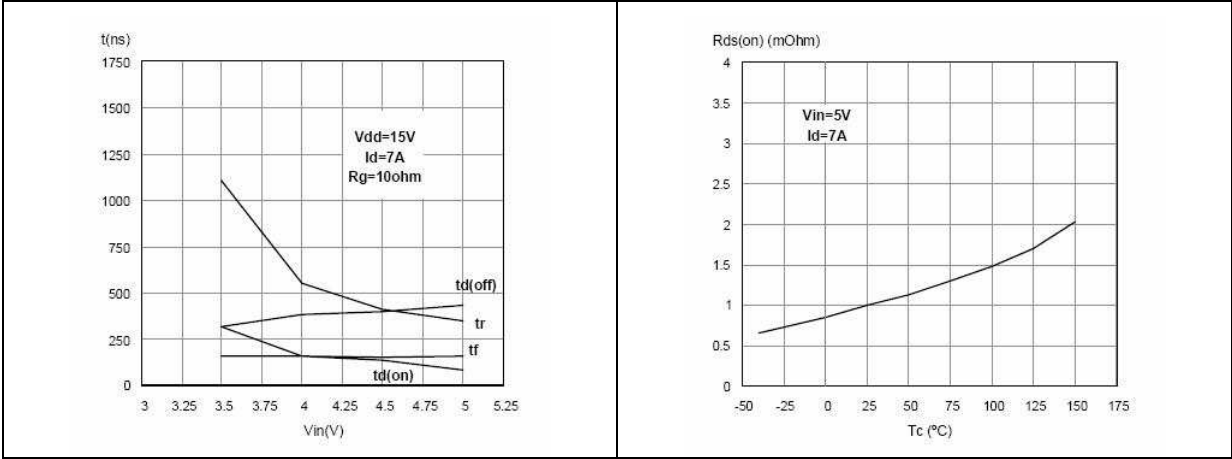


Figure 26. Normalized input threshold voltage vs. temperature

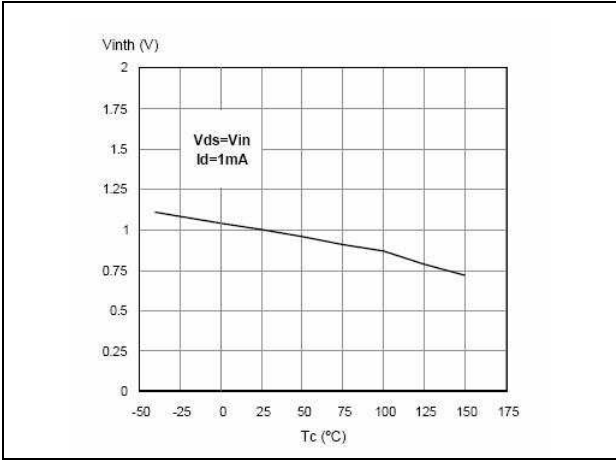


Figure 27. Current limit vs. junction temperatures

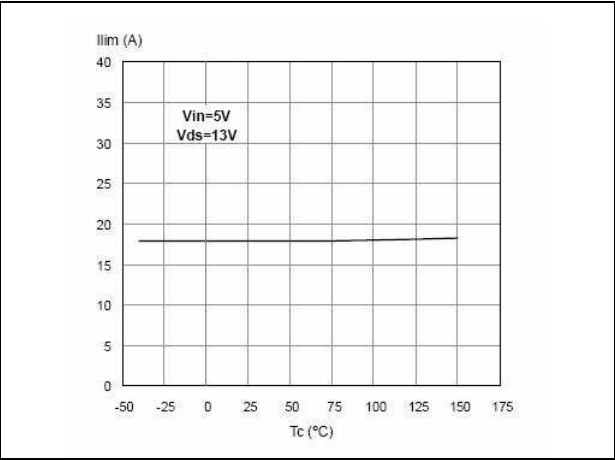


Figure 28. Step response current limit

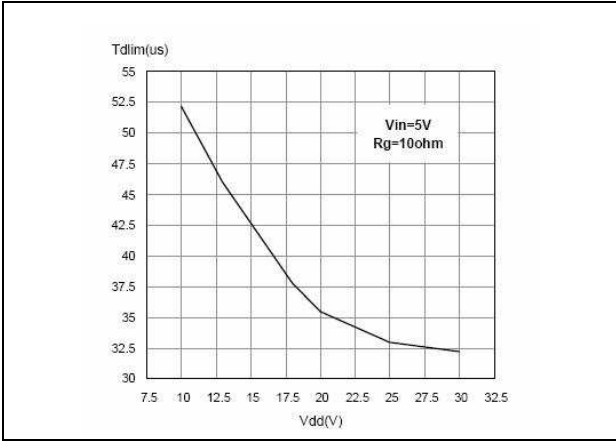
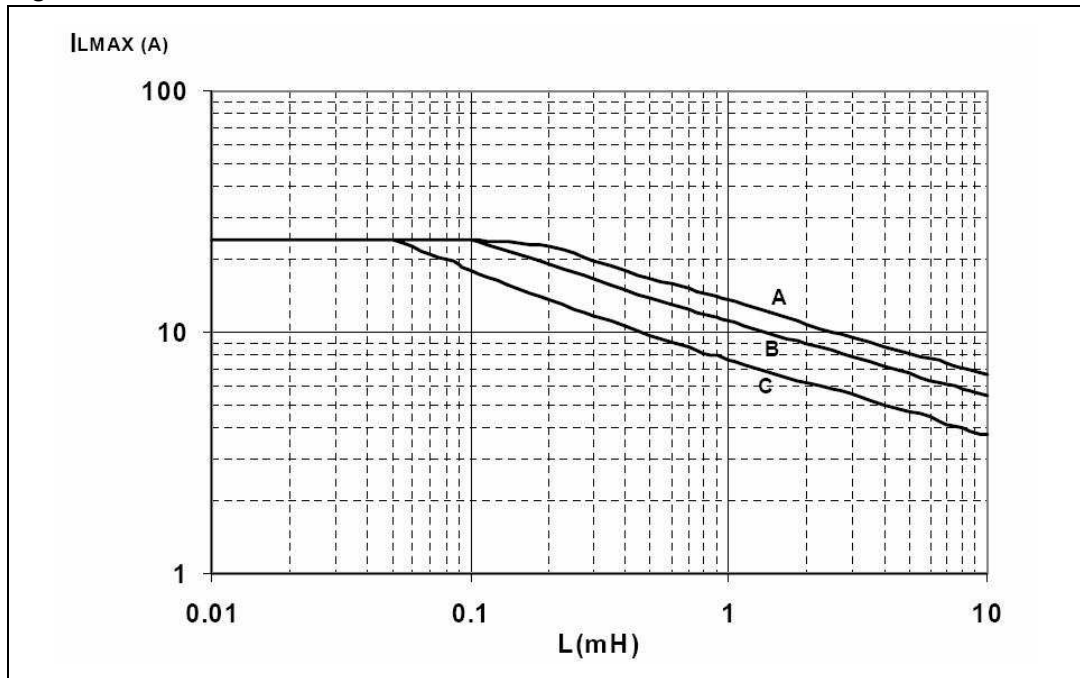


Figure 29. DPAK Maximum turn-off current versus load inductance

Legend:

A= Single pulse at $T_{Jstart}=150^{\circ}\text{C}$

B= Repetitive pulse at $T_{Jstart}=100^{\circ}\text{C}$

C= Repetitive pulse at $T_{Jstart}=125^{\circ}\text{C}$

Conditions:

$V_{CC}=13.5\text{ V}$

Values are generated with $R_L=0\Omega$

In case of repetitive pulses, T_{Jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.

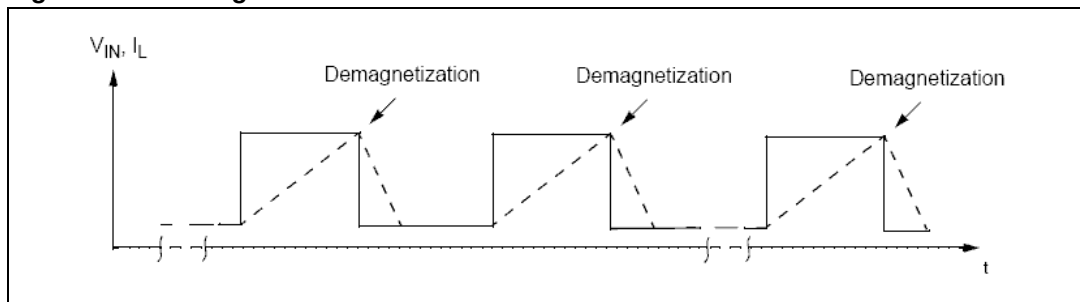
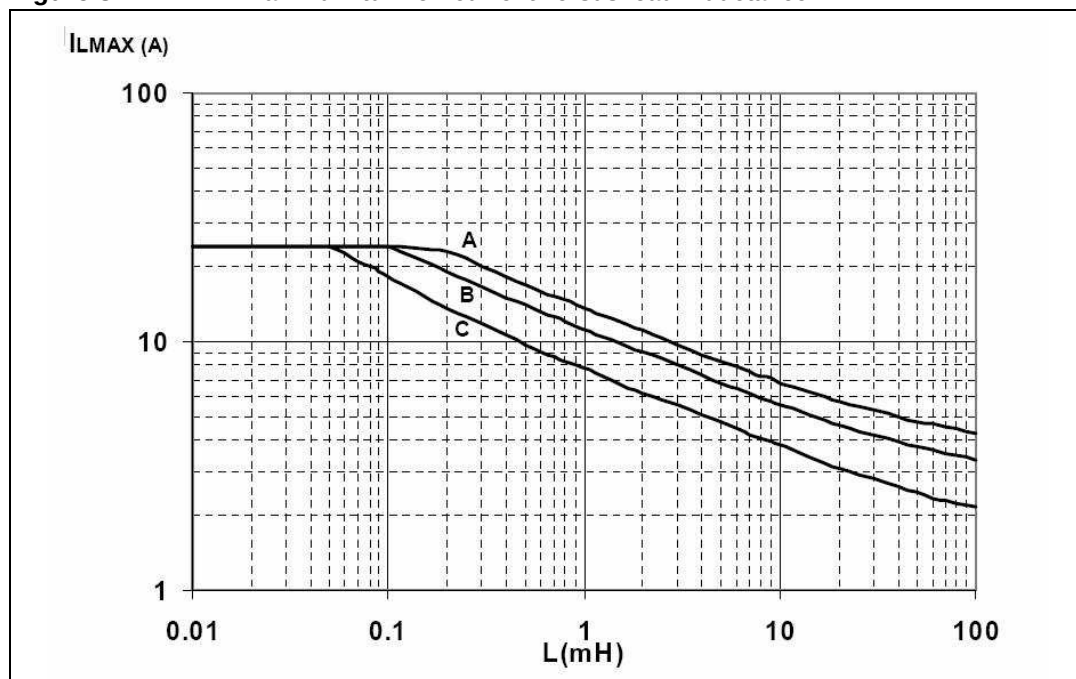
Figure 30. Demagnetization

Figure 31. D²PAK Maximum turn-off current versus load inductance

Legend:

A= Single pulse at $T_{jstart}=150^{\circ}\text{C}$

B= Repetitive pulse at $T_{jstart}=100^{\circ}\text{C}$

C= Repetitive pulse at $T_{jstart}=125^{\circ}\text{C}$

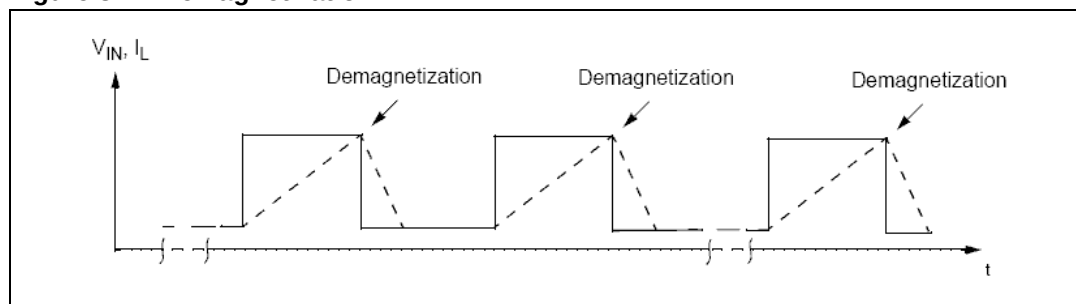
Conditions:

$V_{CC}=13.5\text{ V}$

Values are generated with $R_L=0\Omega$

In case of repetitive pulses, T_{jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.

Figure 32. Demagnetization



4 Package thermal data

4.1 DPAK thermal data

Figure 33. DPAK PC board

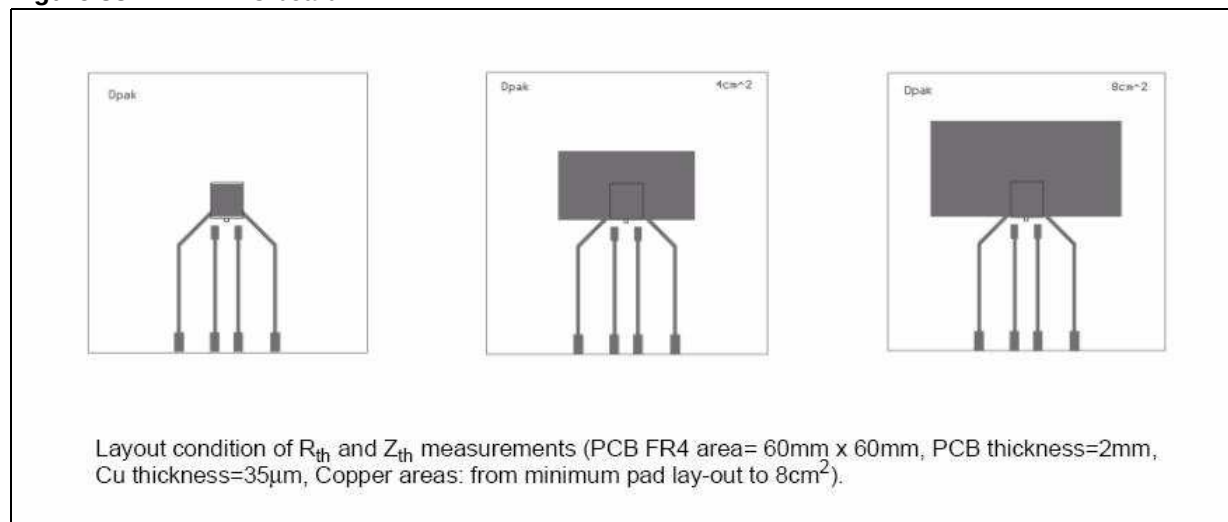


Figure 34. $R_{thj-amb}$ vs PCB copper area in open box free air condition

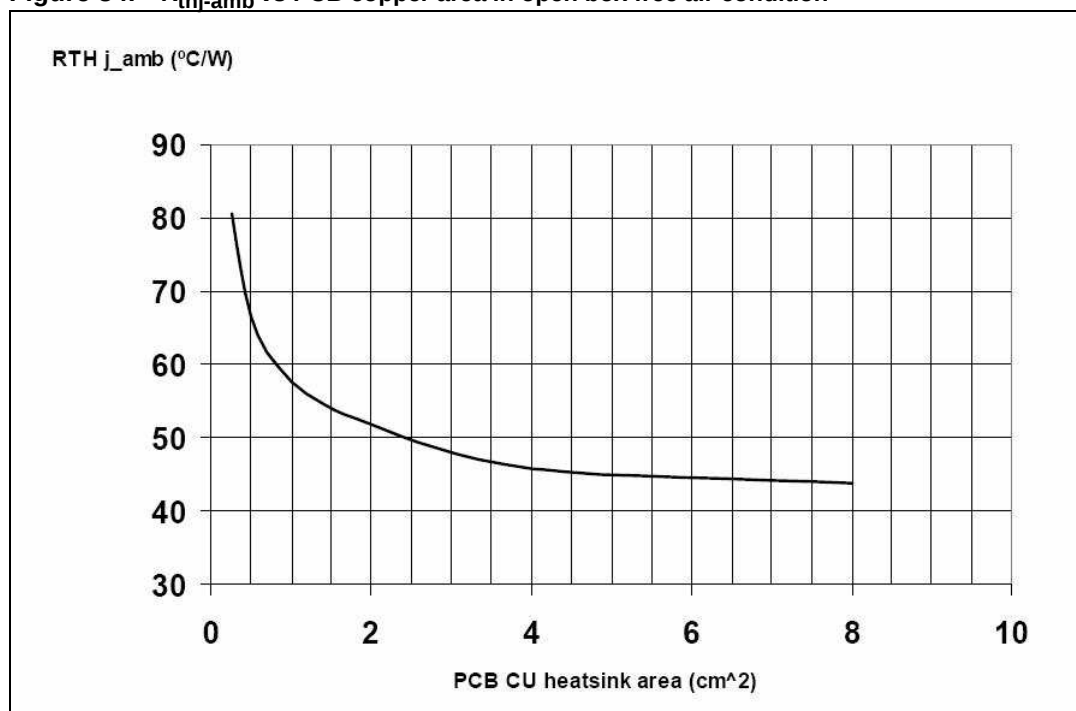


Figure 35. DPAK thermal impedance junction ambient single pulse

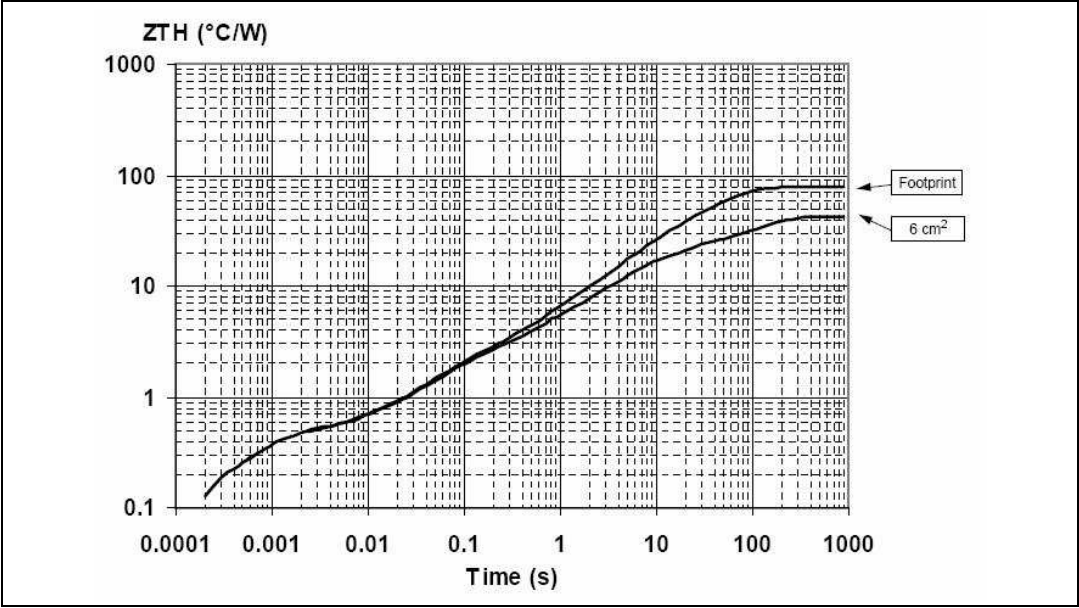
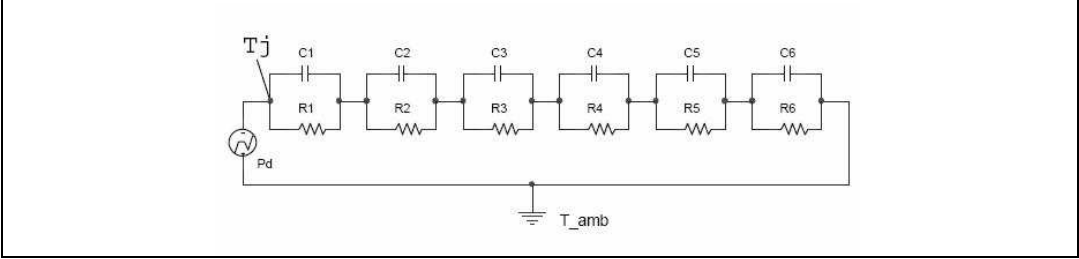


Figure 36. Thermal fitting model of an OMNIFET II in DPAK



Pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Table 5. Thermal parameter

Area/island(cm ²)	Footprint	6
R1 (°C/W)	0.1	
R2 (°C/W)	0.35	
R3 (°C/W)	1.20	
R4 (°C/W)	2	
R5 (°C/W)	15	
R6 (°C/W)	61	24
C1 (W.s/°C)	0.0006	
C2 (W.s/°C)	0.0021	
C3 (W.s/°C)	0.05	

Table 5. Thermal parameter (continued)

Area/island(cm ²)	Footprint	6
C4 (W.s/°C)	0.3	
C5 (W.s/°C)	0.45	
C6 (W.s/°C)	0.8	5

4.2 D²PAK thermal data

Figure 37. D²PAK PC board

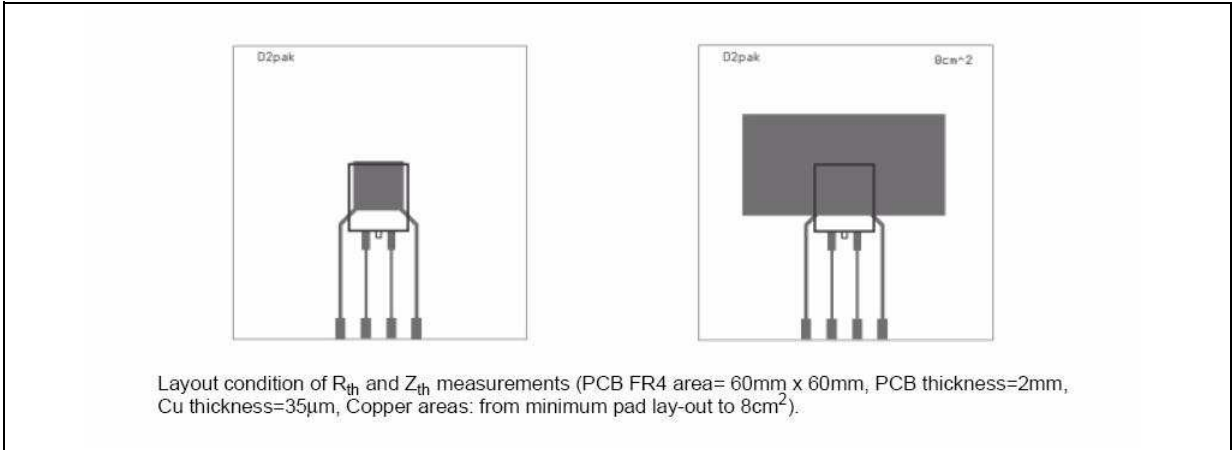


Figure 38. Rthj-amb vs PCB copper area in open box free air condition

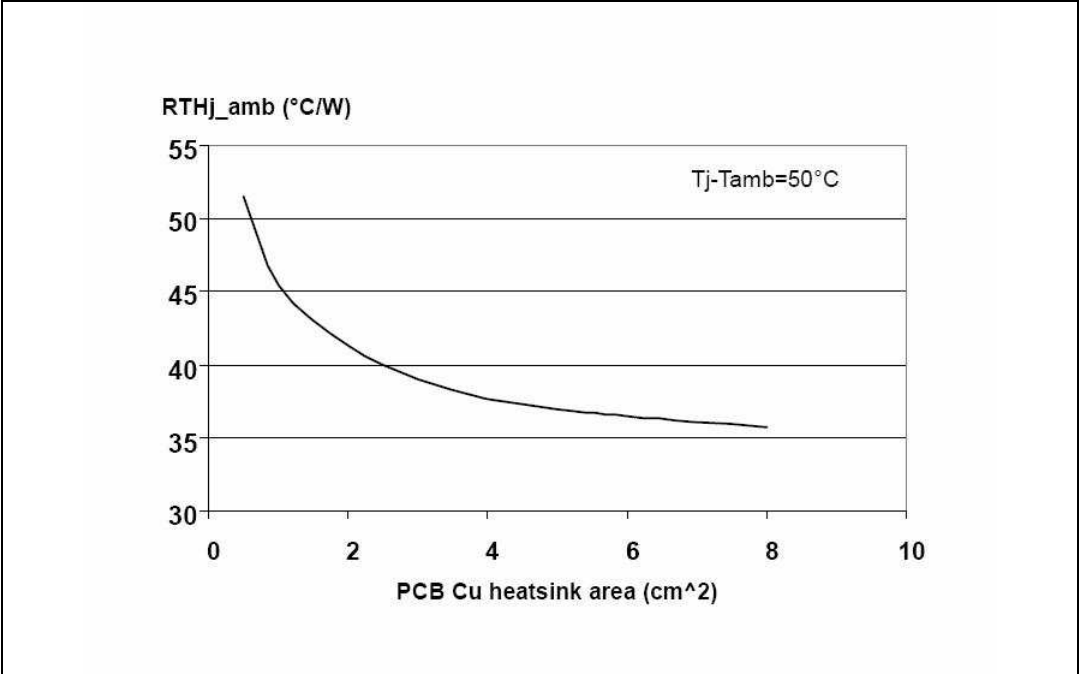


Figure 39. D²PAK thermal impedance junction ambient single pulse

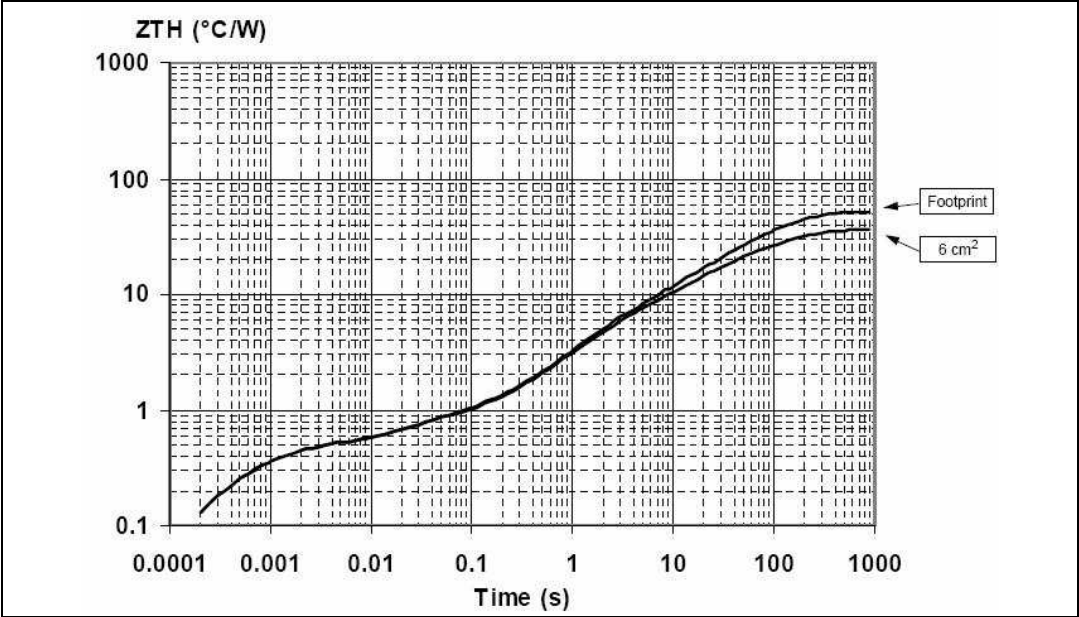
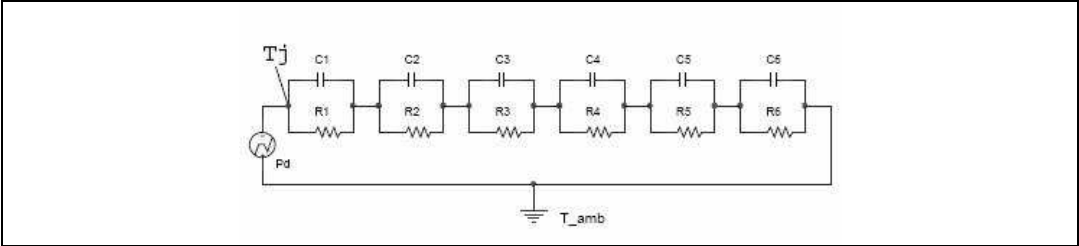


Figure 40. Thermal fitting model of an OMNIFET II in D²PAK



Pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Table 6. Thermal parameter

Area/island(cm ²)	Footprint	6
R1 (°C/W)	0.1	
R2 (°C/W)	0.35	
R3 (°C/W)	0.3	
R4 (°C/W)	4	
R5 (°C/W)	9	
R6 (°C/W)	37	22
C1 (W.s/°C)	0.0006	
C2 (W.s/°C)	2.10E-03	
C3 (W.s/°C)	8.00E-02	

Table 6. Thermal parameter (continued)

Area/island(cm ²)	Footprint	6
C4 (W.s/°C)	0.45	
C5 (W.s/°C)	2	
C6 (W.s/°C)	3	5

5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.

ECOPACK® is an ST trademark.

Figure 41. TO-251 (IPAK) mechanical data

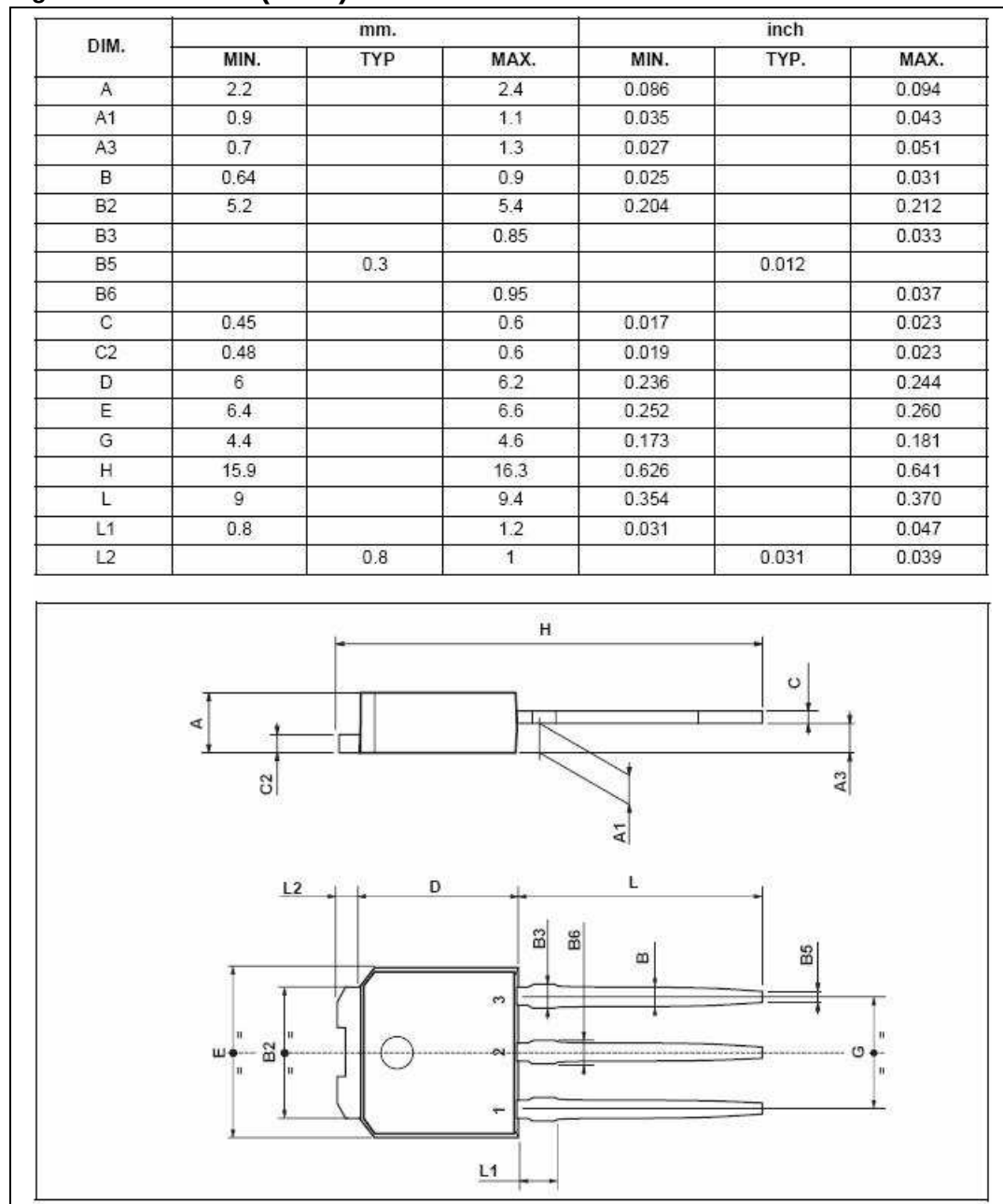


Figure 42. D²PAK mechanical data

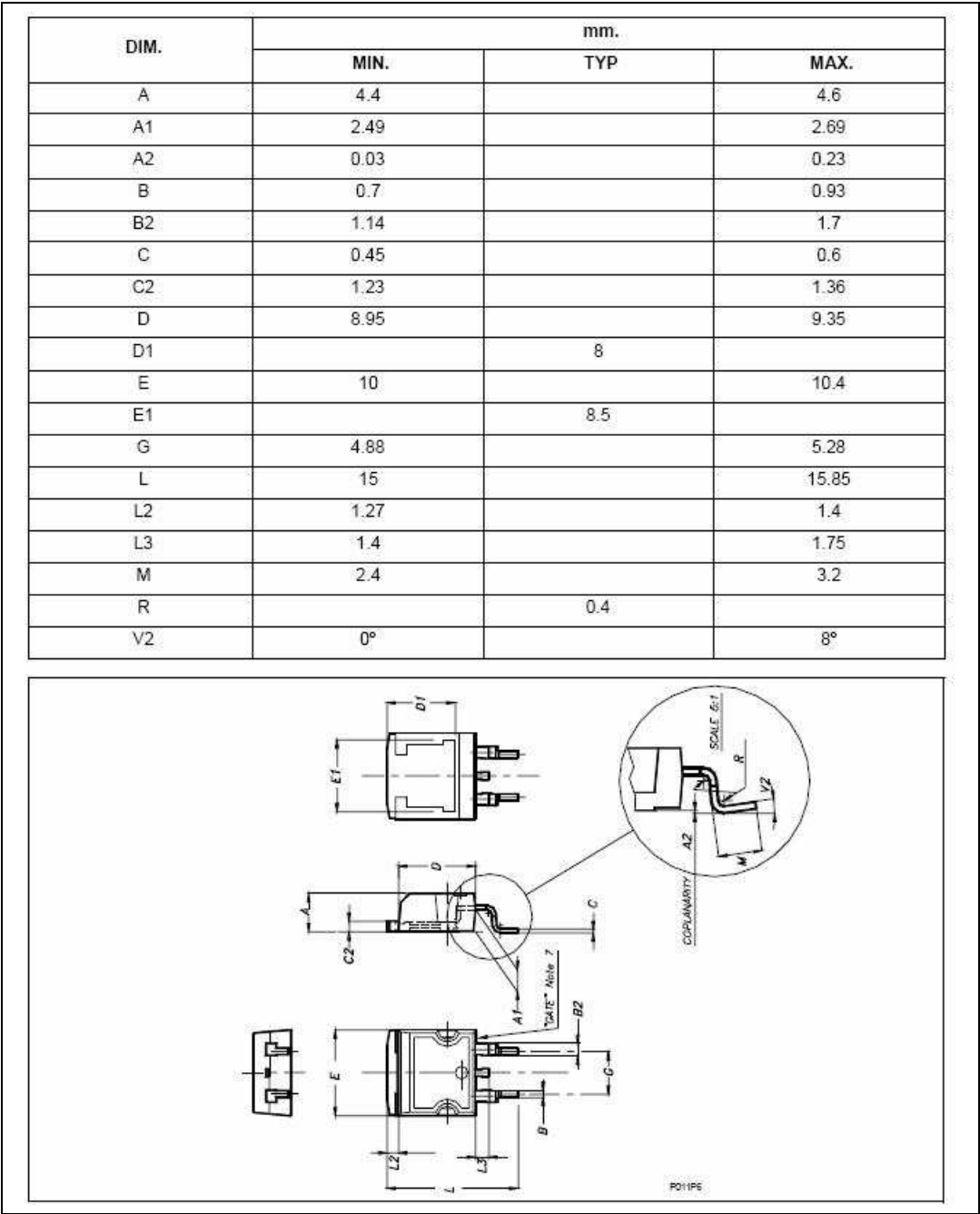
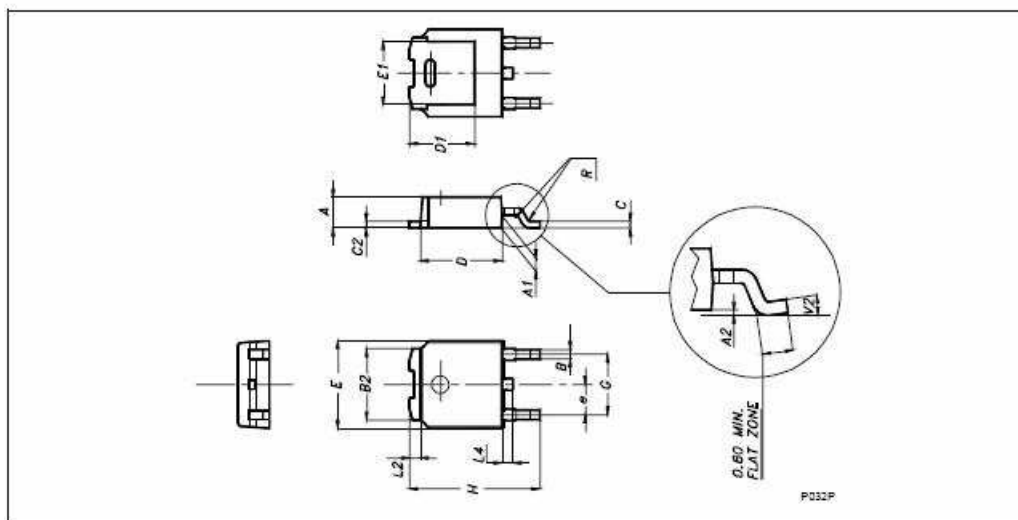


Figure 43. TO-252 (DPAK) mechanical data

DIM.	mm.		
	MIN.	TYP	MAX.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
B	0.64		0.90
B2	5.20		5.40
C	0.45		0.60
C2	0.48		0.60
D	6.00		6.20
D1		5.1	
E	6.40		6.60
E1		4.7	
e		2.28	
G	4.40		4.60
H	9.35		10.10
L2		0.8	
L4	0.60		1.00
R		0.2	
V2	0°	8°	
Package Weight	Gr. 0.29		



6 Revision history

Table 7. Document revision history

Date	Revision	Changes
21-Jun-2004	6	Initial release.
03-Apr-2009	7	Document reformatted. Added Table 1: Device summary on page 1 . Updated Section 5: Package information on page 21

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